1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-30612G

2. Structure :

2-1. Planar type : P/N Diode
2-2. Electrodes :
Top side : Gold pad.
Back side : Gold layer.

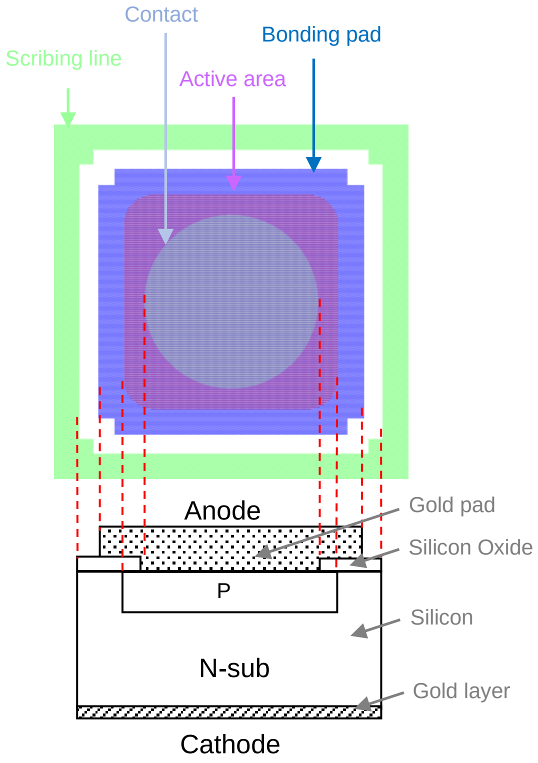
3. Size :

3-1. ※1Chip size : 6.88 mils x 6.88 mils (0.175 mm x 0.175 mm).
3-2. Chip thickness : 4.0 ± 1.0 mils (0.100 ± 0.0254 mm).
3-3. Active area : 4.1 mils x 4.1 mils (0.105 mm x 0.105 mm).
3-4. ※2Bonding pad : 4.8 mils x 4.8 mils (0.122 mm x 0.122 mm).
3-5. Pattern drawing : Refer to the attached drawing.

※1Including scribing line. The chip size is about $(0.150\pm0.015)^2$mm^2 after dicing.
※2 The wire bonding pad dimension is $(0.122\pm0.015)^2$mm^2 after etching.

4. Electrical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	V_R=9V Ee=0mW/cm^2			100	nA
Zener Voltage	Vz	I_Z=5mA Ee=0mW/cm^2	10		14	V
Forward Voltage	Vf	I_F=20mA Ee=0mW/cm^2	0.75		1.2	V



Equivalent Circuit